

PBSS5160U

60 V, 1 A PNP low V_{CEsat} (BISS) transistor

Rev. 03 — 11 August 2005

Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT323 (SC-70) Surface Mounted Device (SMD) plastic package.

NPN complement: PBSS4160U.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- High voltage DC-to-DC conversion
- High voltage MOSFET gate driving
- High voltage motor control
- High voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-60	V
I_C	collector current		[1]	-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-2	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -1$ A; $I_B = -100$ mA	[2]	255	340	m Ω

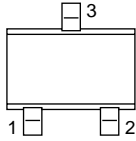
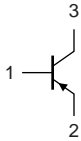
[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[2] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

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2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter		
3	collector		

sym013

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PBSS5160U	SC-70	plastic surface mounted package; 3 leads	SOT323

4. Marking

Table 4: Marking codes

Type number	Marking code ^[1]
PBSS5160U	53*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

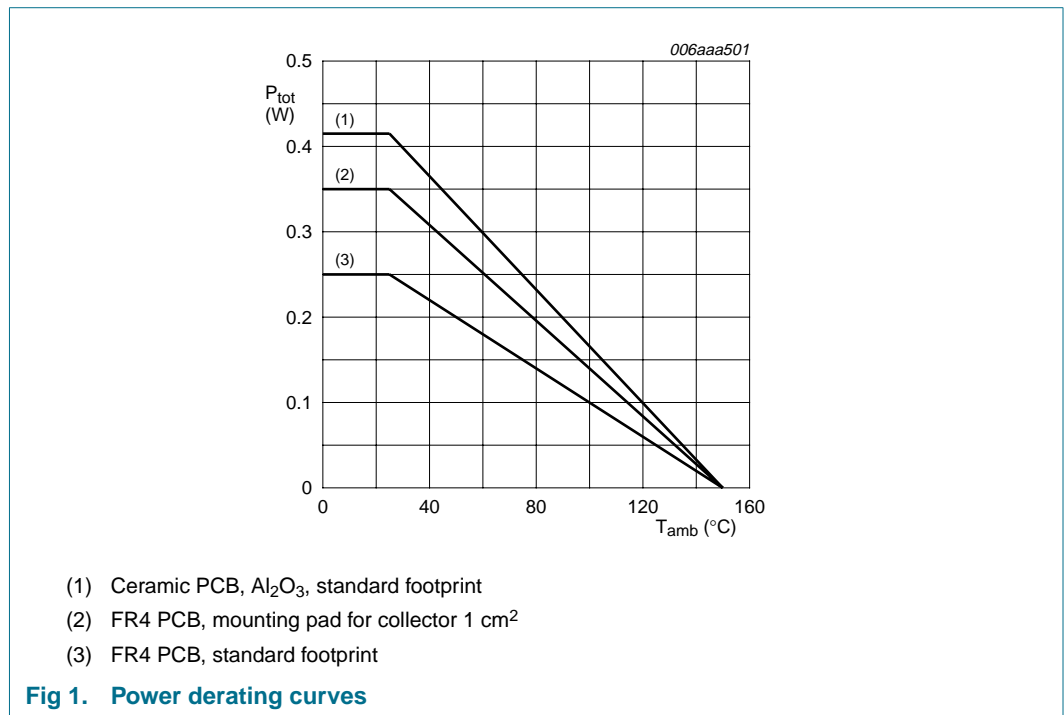
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-80	V
V_{CEO}	collector-emitter voltage	open base	-	-60	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I_C	collector current	[1]	-	-0.7	A
		[2]	-	-0.86	A
		[3]	-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-2	A
I_B	base current		-	-300	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	-1	A

Table 5: Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1] -	250	mW
			[2] -	350	mW
			[3] -	415	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
			[2]	-	-	357	K/W
			[3]	-	-	301	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	150	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

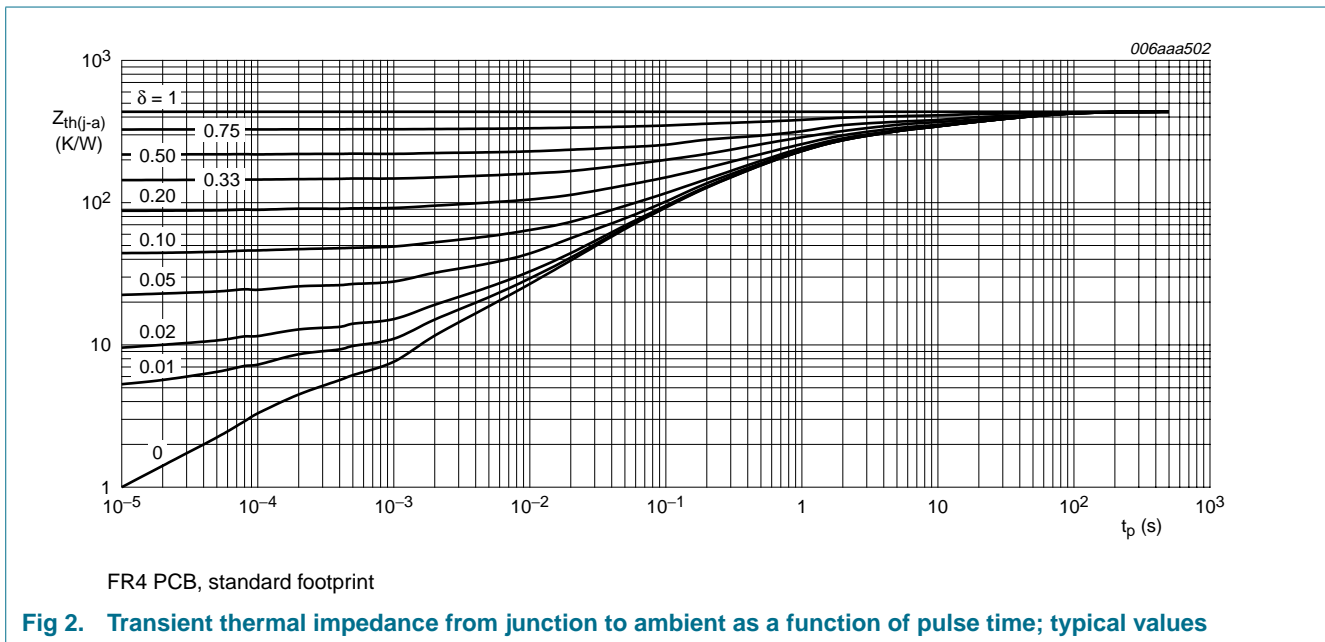
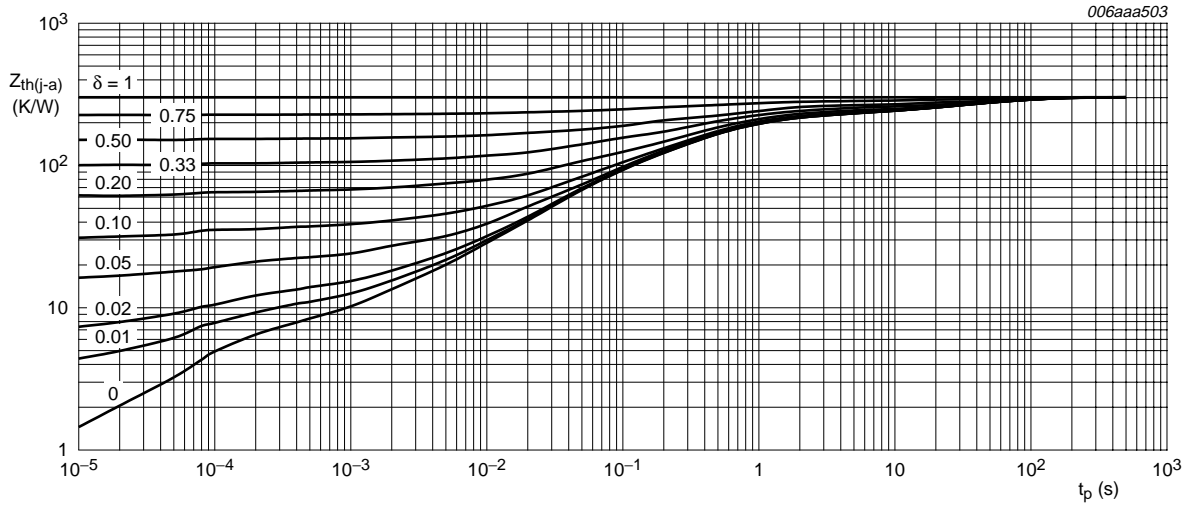
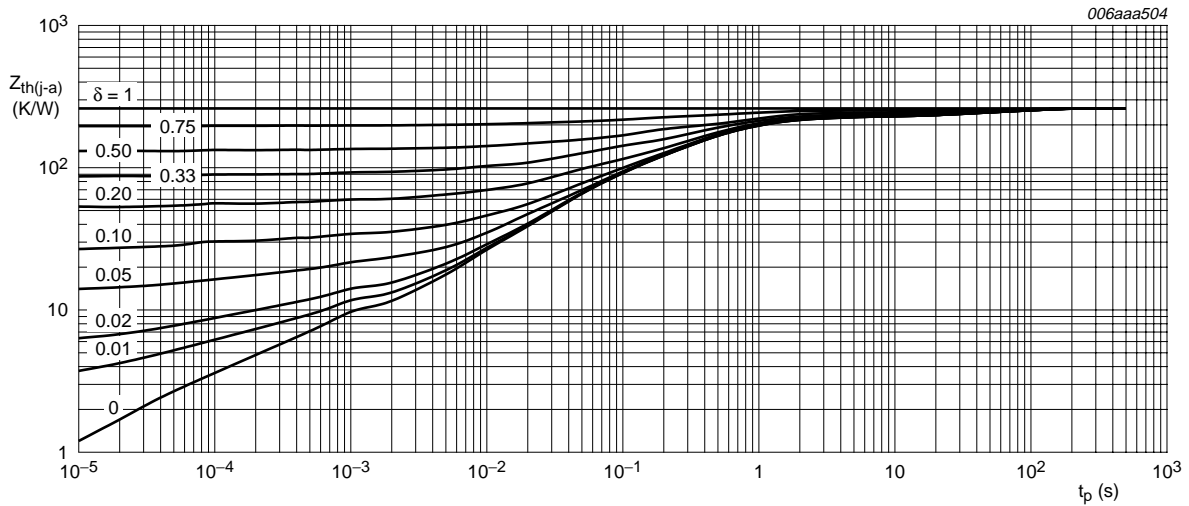


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

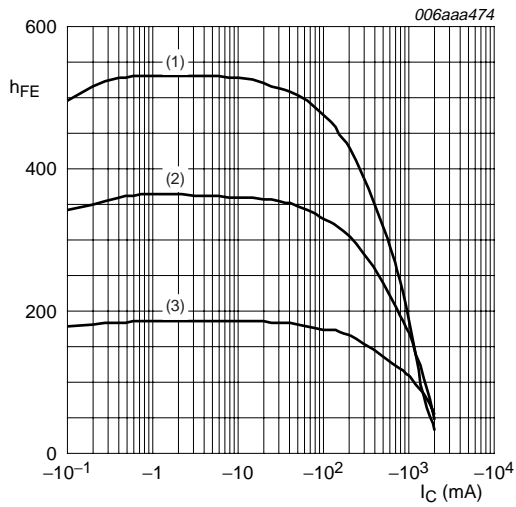
7. Characteristics

Table 7: Characteristics

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified.

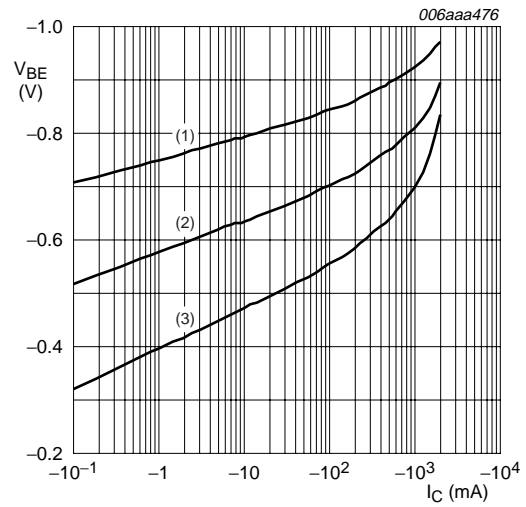
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -60\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
		$V_{CB} = -60\text{ V}; I_E = 0\text{ A}; T_j = 150^\circ\text{C}$	-	-	-50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -60\text{ V}; V_{BE} = 0\text{ V}$	-	-	-100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	200	350	-	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	[1] 150	250	-	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	[1] 100	160	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	-	-110	-175	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	-	-135	-180	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1] -	-255	-340	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	-	-0.95	-1.1	V
R_{CEsat}	collector-emitter saturation resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1] -	255	340	m Ω
V_{BEon}	base-emitter turn-on voltage	$I_C = -1\text{ A}; V_{CE} = -5\text{ V}$	-	-0.82	-0.9	V
t_d	delay time	$I_C = -0.5\text{ A}; I_{Bon} = -25\text{ mA}; I_{Boff} = 25\text{ mA}$	-	11	-	ns
t_r	rise time		-	30	-	ns
t_{on}	turn-on time		-	41	-	ns
t_s	storage time		-	205	-	ns
t_f	fall time		-	55	-	ns
t_{off}	turn-off time		-	260	-	ns
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	150	185	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	9	15	pF

[1] Pulse test: $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02$.



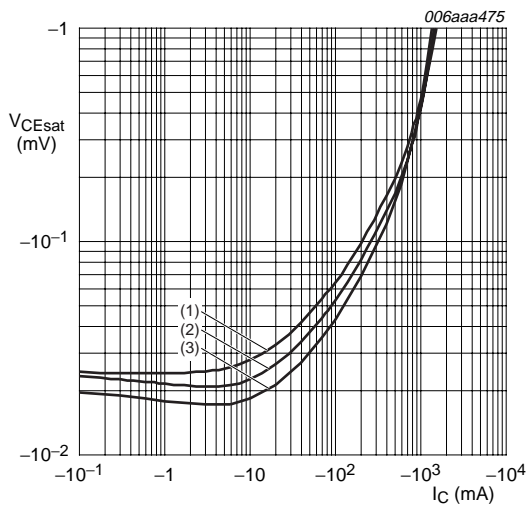
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 5. DC current gain as a function of collector current; typical values



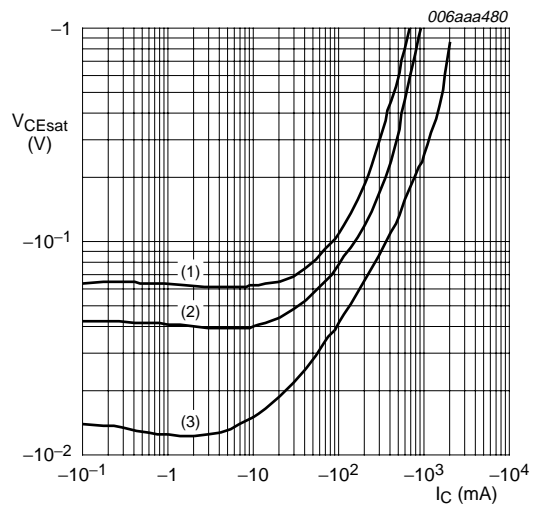
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 6. Base-emitter voltage as a function of collector current; typical values



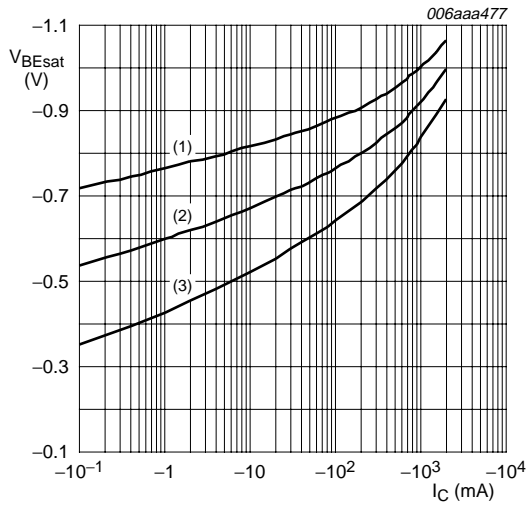
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



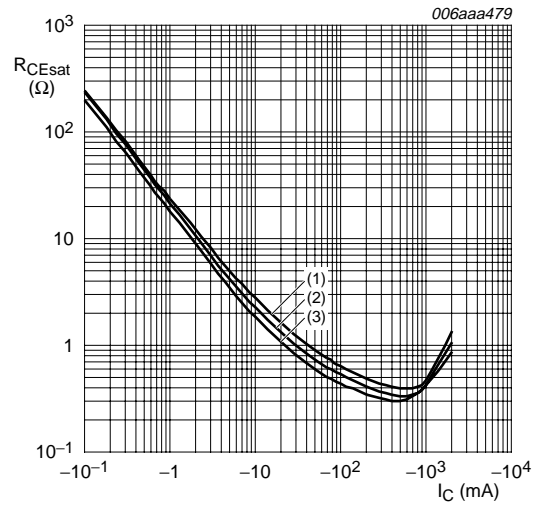
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



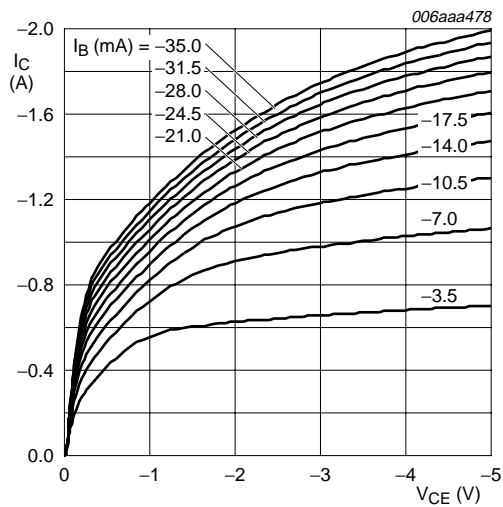
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values



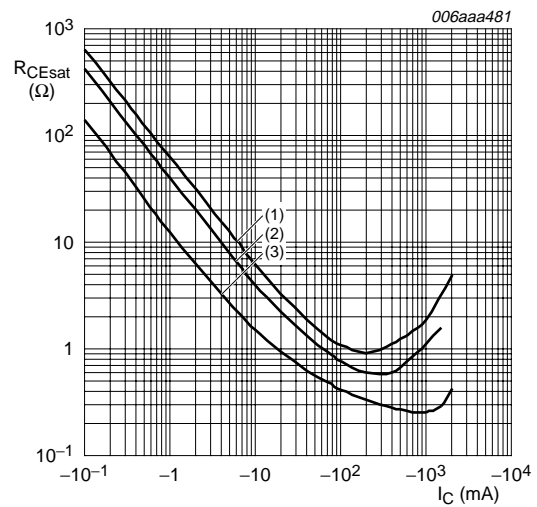
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$

Fig 11. Collector current as a function of collector-emitter voltage; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

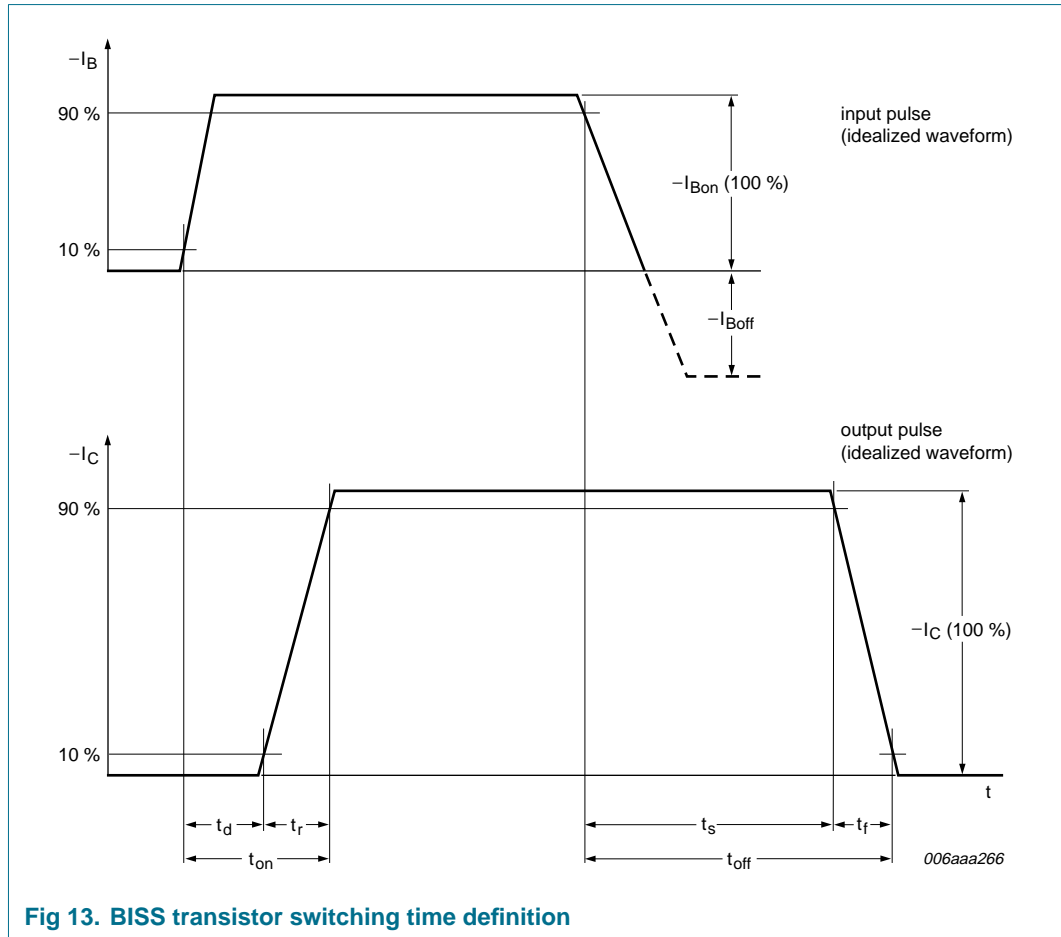
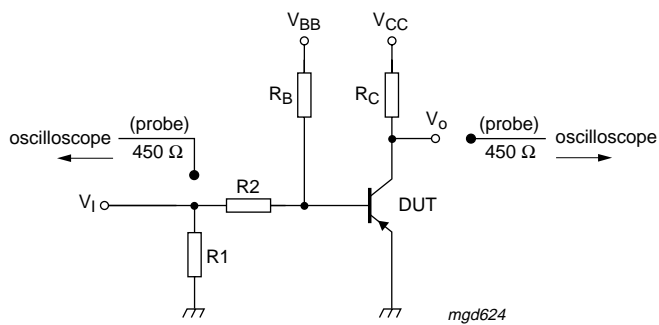


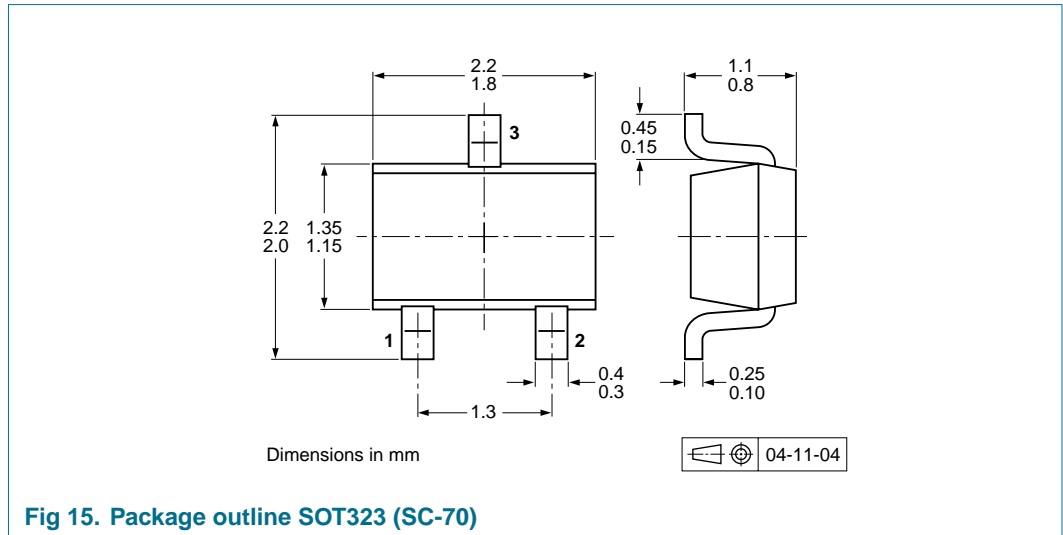
Fig 13. BISS transistor switching time definition



$I_C = -0.5\text{ A}$; $I_{B_{on}} = -25\text{ mA}$; $I_{B_{off}} = 25\text{ mA}$; $R_1 = \text{open}$; $R_2 = 100\ \Omega$; $R_B = 300\ \Omega$; $R_C = 20\ \Omega$

Fig 14. Test circuit for switching times

9. Package outline



10. Packing information

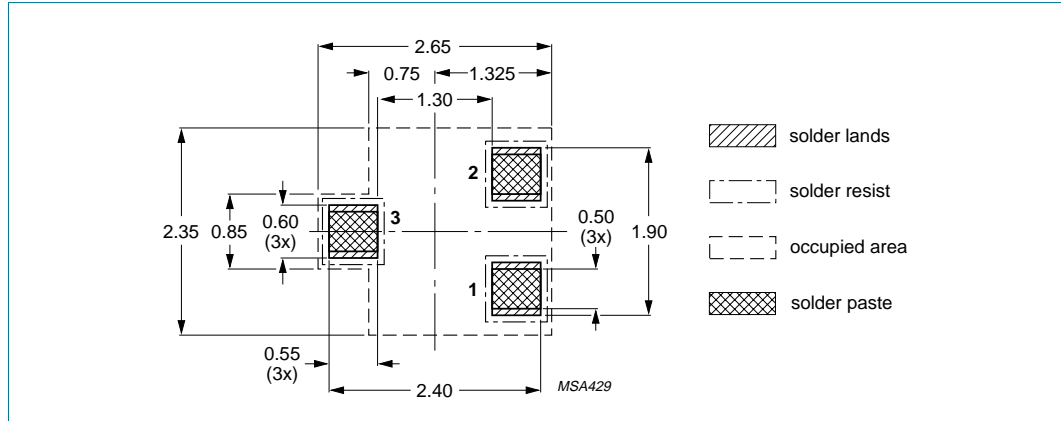
Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [\[1\]](#)

Type number	Package	Description	Packing quantity	
			3000	10000
PBSS5160U	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

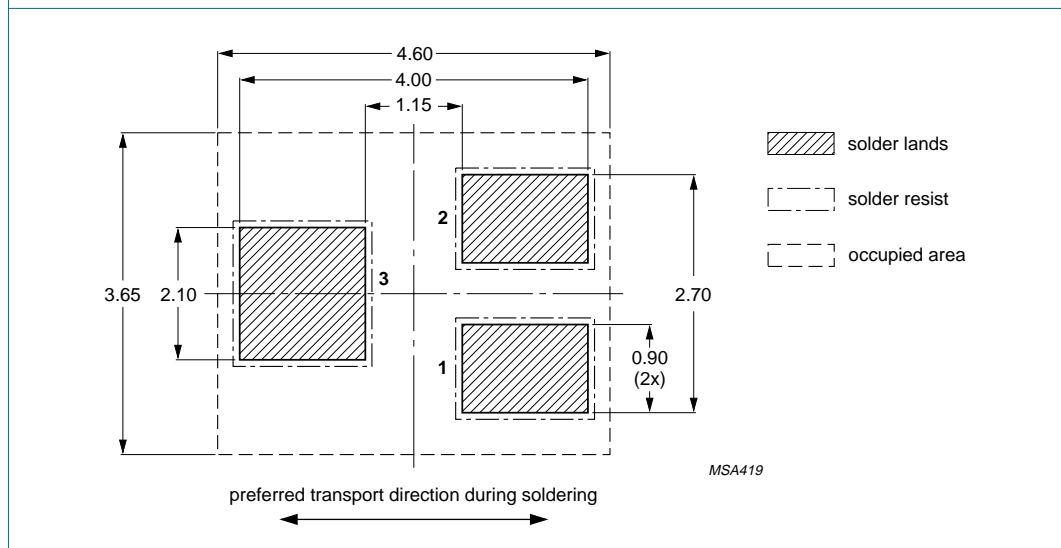
[1] For further information and the availability of packing methods, see [Section 17](#).

11. Soldering



Dimensions in mm

Fig 16. Reflow soldering footprint



Dimensions in mm

Fig 17. Wave soldering footprint

12. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PBSS5160U_3	20050811	Product data sheet	-	9397 750 15184	PBSS5160U_2
Modifications:					
			<ul style="list-style-type: none"> • Product status changed • Section 1.2 “Features”: amended • Section 1.3 “Applications”: amended • Table 1: renamed parameter R_{CEsat} to collector-emitter saturation resistance • Table 4 “Marking codes”: enhanced table note section • Table 6 “Thermal characteristics”: enhanced • Figure 3 and 4: added • Table 7 “Characteristics”: added switching time parameters t_d, t_r, t_{on}, t_s, t_f and t_{off} • Table 7: renamed parameter R_{CEsat} to collector-emitter saturation resistance • Figure 10 and 12: renamed parameter R_{CEsat} to collector-emitter saturation resistance • Section 8 “Test information”: added • Figure 15: superseded by minimized package outline drawing • Section 10 “Packing information”: added • Section 11 “Soldering”: added • Section 16 “Trademarks”: added 		
PBSS5160U_2	20040809	Objective data sheet	-	9397 750 13265	PBSS5160U_1
PBSS5160U_1	20040503	Objective data sheet	-	9397 750 12885	-

13. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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